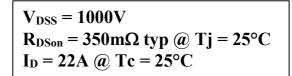
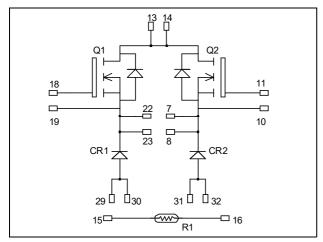


Dual Buck chopper MOSFET Power Module





Application

- AC and DC motor control
- Switched Mode Power Supplies

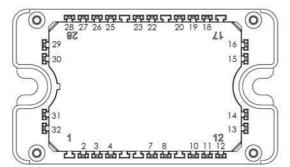
Features

• Power MOS 7® MOSFETs

- Low R_{DSon}
- Low input and Miller capacitance
- Low gate charge
- Avalanche energy rated
- Very rugged
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring



- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single buck of twice the current capability
- RoHS Compliant



All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (per MOSFET)

Symbol	Parameter		Max ratings	Unit
V_{DSS}	Drain - Source Voltage		1000	V
I_D	Continuous Drain Current	$T_c = 25$ °C	22	
1D	Continuous Diani Current	$T_c = 80$ °C	17	A
I_{DM}	Pulsed Drain current		88	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		420	$m\Omega$
P_{D}	Power Dissipation	390	W	
I_{AR}	Avalanche current (repetitive and non repetitive)		25	A
E _{AR}	Repetitive Avalanche Energy		50	T
E_{AS}	ngle Pulse Avalanche Energy		3000	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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Electrical Characteristics (per MOSFET)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$			100	μA
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 11A$		350	420	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.5 \text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			±150	nA

Dynamic Characteristics (per MOSFET)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		5.2		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		0.88		nF
C_{rss}	Reverse Transfer Capacitance	f=1MHz		0.16		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		186		
Q_{gs}	Gate – Source Charge	$V_{\rm Bus} = 500 V$		24		nC
Q_{gd}	Gate – Drain Charge	$I_D = 22A$		122		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		18		
$T_{\rm r}$	Rise Time	$V_{GS} = 15V$		12		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 670V$ $I_{\text{D}} = 22A$		155		ns
T_{f}	Fall Time	$R_G = 5\Omega$		40		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 22A, R_G = 5\Omega$		900		т
E_{off}	Turn-off Switching Energy			623		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 22A, R_G = 5\Omega$		1423		
E_{off}	Turn-off Switching Energy			779		μJ
R_{thJC}	Junction to Case Thermal Resistance	2			0.32	°C/W

Chopper Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					1000	V
I_{RM}	Reverse Leakage Current	$V_R = 1000V$				250	μA
I_{F}	DC Forward Current		$T_c = 70$ °C		30		A
		$I_F = 30A$	$I_F = 30A$		1.9	2.3	
V_{F}	Diode Forward Voltage	$I_F = 60A$			2.2		V
		$I_F = 30A$	$T_j = 125$ °C		1.7		
+	Reverse Recovery Time	Ι_ = 20 Δ	$T_j = 25$ °C		290		12 G
t_{rr}	Reverse Recovery Time		$T_j = 125$ °C		390		ns
Qrr	Reverse Recovery Charge	di/dt=200A/μs	$T_j = 25$ °C		670		nC
			$T_j = 125$ °C		2350		iic
R_{thJC}	Junction to Case Thermal Resistance					1.2	°C/W



Thermal and package characteristics

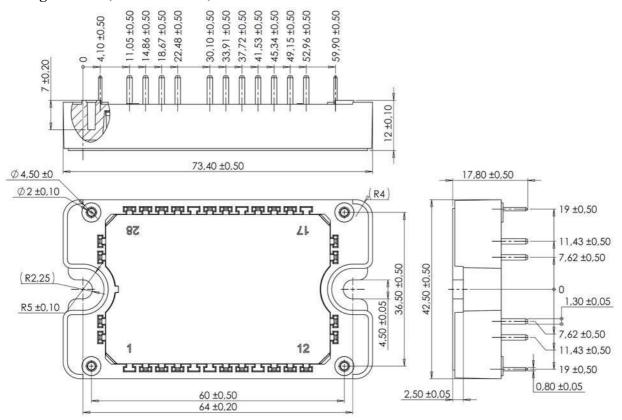
Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
$T_{\rm J}$	Operating junction temperature range			-40	150	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max - 25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature				125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C	C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T _C =100°C		4		%

$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \begin{array}{l} \text{T: Thermistor temperature} \\ R_{T}: \text{ Thermistor value at T} \end{array}$$

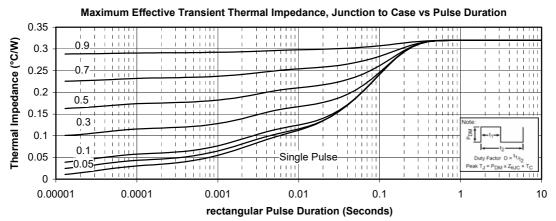
Package outline (dimensions in mm)

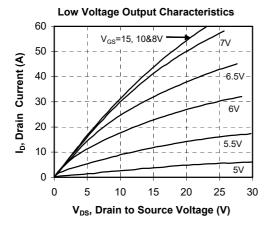


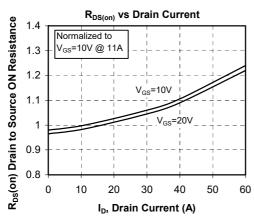
See application note 1906 - Mounting Instructions for SP3F Power Modules on $\underline{www.microsemi.com}$

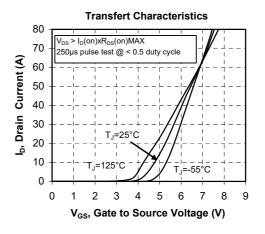


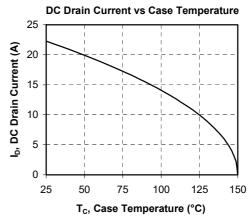
Typical Performance Curve







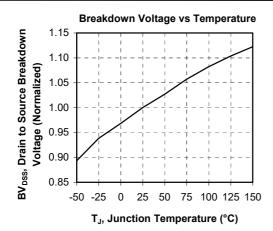


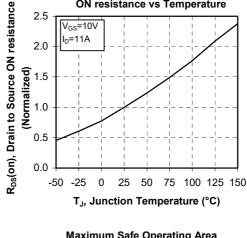


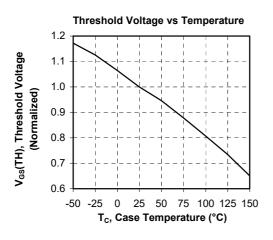
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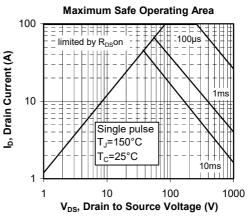


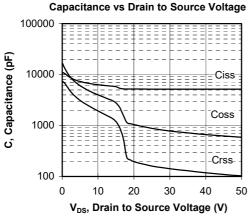
ON resistance vs Temperature

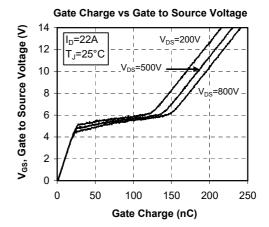




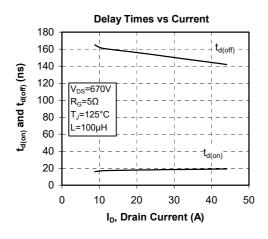


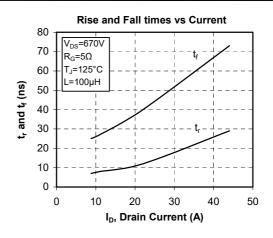


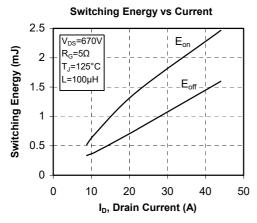


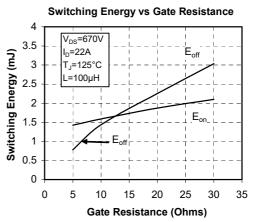


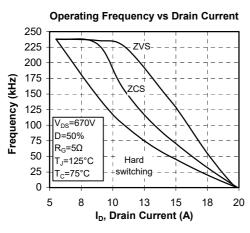


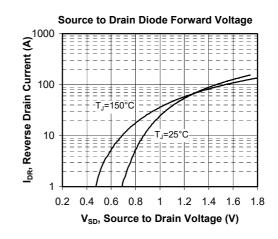












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